

	Type	L #	Hits	Search Text	DBs	Time Stamp	Com men ts	Er ro r De fi ni ti on	Er ro rs
1	BRS	L2	36	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:34			
2	BRS	L3	130	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:59			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
3	BRS	L4	131	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step\$5 with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:35			
4	BRS	L5	21	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and semiconductor with (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step\$5 with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:36			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
5	BRS	L6	18	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and semiconductor with (carrier or electron or hole) with ("100" or "010" or "001") and step\$5 with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:39			
6	BRS	L7	13	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole) with ("100" or "010" or "001") with direction and step\$5 with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:40			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
7	BRS	L8	13	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") with direction and step\$5 with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:44			
8	BRS	L9	114	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step\$5 with (anneal\$4 or heat\$4 or thermal) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:45			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
9	BRS	L10	0	(438/198).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:46			
10	BRS	L12	0	(438/158).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:47			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
11	BRS	L11	2	(438/149).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:48			
12	BRS	L13	0	(438/492).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:48			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	L14	0	(438/503).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:48			
14	BRS	L15	1	(438/507).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:48			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
15	BRS	L16	2	(438/268).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:48			
16	BRS	L17	3	(438/273).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:49			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
17	BRS	L18	2	(438/285).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:49			
18	BRS	L19	2	(438/285).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step and (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:49			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
19	BRS	L20	83	("438"/\$).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step and (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:50			
20	BRS	L21	12	("438"/\$).ccls. and (silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with direction with ("100" or "010" or "001") and step and (anneal\$4 or heat\$4 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:53			
21	IS&R	L22	2	("5212404").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:53			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
22	BRS	L23	4	("5212404").URPN.	USPAT	2006/01/04 01:54			
23	IS&RL	L24	3	("5436468").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:54			
24	BRS	L25	10	("5436468").URPN.	USPAT	2006/01/04 01:56			
25	BRS	L26	37	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal) and mos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 01:59			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
26	BRS	L27	4	(silicon or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal) and mos and vertical\$4 with channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 02:13			
27	BRS	L28	4	(silicon or gaas or semiconductor or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and step with (anneal\$4 or heat\$4 or thermal) and mos and vertical\$4 with channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 02:13			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
28	BRS	L29	9	(silicon or gaas or semiconductor or substrate) with (angle or inclin\$5 or slant\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and (anneal\$4 or heat\$4 or thermal) and mos and vertical\$4 with channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 02:18			
29	BRS	L30	12	(silicon or gaas or semiconductor or substrate) with (angle or inclin\$5 or slant\$4 or tilt\$4) with ("100" or "010" or "001") and (carrier or electron or hole or mobility) with ("100" or "010" or "001") and (anneal\$4 or heat\$4 or thermal) and mos and vertical\$4 with channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/01/04 02:18			